Low-Temperature Growth of Epitaxial III-Nitride Films via Hollow Cathode Plasma Atomic Layer Deposition

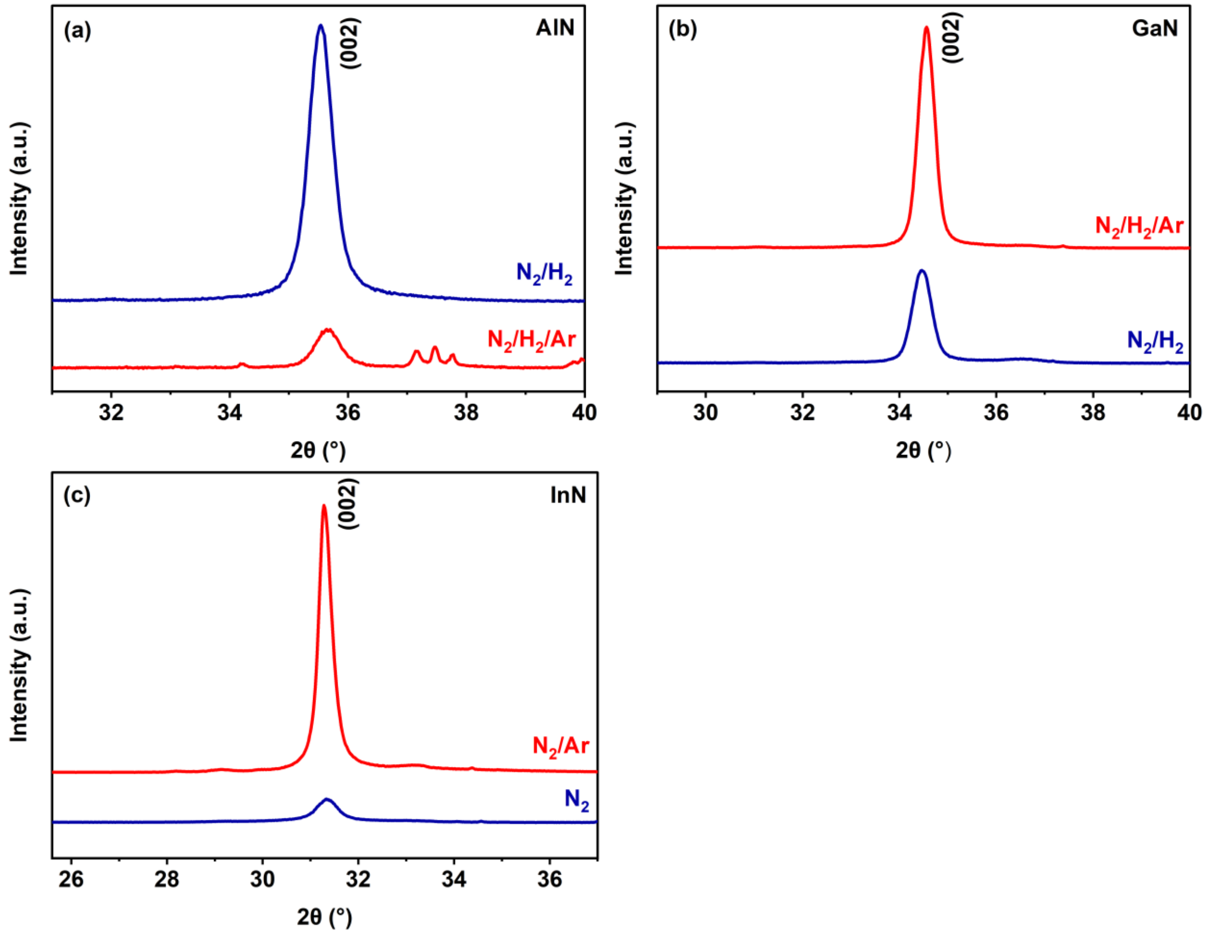

Figure 1. θ-2θ XRD measurements of III-nitride films grown with different plasma gas compositions. (a) AlN, (b) GaN, and (c) InN.

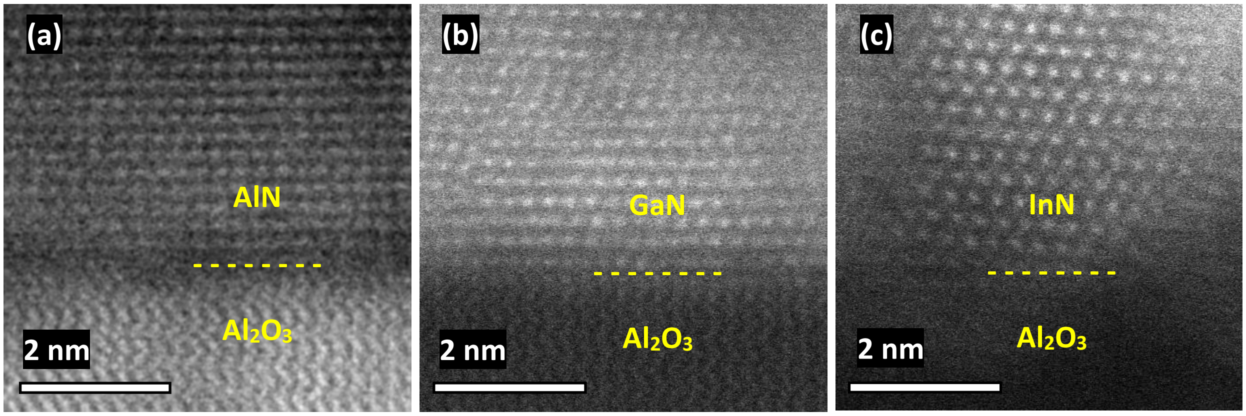

Figure 2. High-angle annular dark-field (HAADF) STEM images taken at the interfaces of each III-nitride film with sapphire. (a) AlN, (b) GaN, and (c) InN.